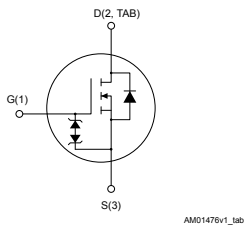
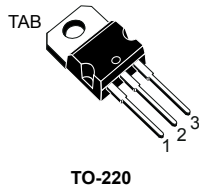


N-channel 600 V, 70 mΩ typ., 36 A, MDmesh DM6 Power MOSFET in a TO-220 package



Features

| Order code | V _{DS} | R _{DS(on)} max. | I _D |
|-------------|-----------------|--------------------------|----------------|
| STP50N60DM6 | 600 V | 80 mΩ | 36 A |

- Fast-recovery body diode
- Lower R_{DS(on)} per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in R_{DS(on)} per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.



Product status link

[STP50N60DM6](#)

Product summary

| | |
|-------------------|-------------|
| Order code | STP50N60DM6 |
| Marking | 50N60DM6 |
| Package | TO-220 |
| Packing | Tube |

1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|-----------------------------------------------------------------|------------|------------------|
| V_{GS} | Gate-source voltage | ± 25 | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 36 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 23 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 137 | A |
| P_{TOT} | Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 250 | W |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 100 | V/ns |
| $di/dt^{(2)}$ | Peak diode recovery current slope | 1000 | A/ μs |
| $dv/dt^{(3)}$ | MOSFET dv/dt ruggedness | 100 | V/ns |
| T_J | Operating junction temperature range | -55 to 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature range | | |

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 36\text{ A}$, $V_{DS}(\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DS} \leq 480\text{ V}$.

Table 2. Thermal data

| Symbol | Parameter | Value | Unit |
|----------------|----------------------------------|-------|--------------------|
| $R_{thj-case}$ | Thermal resistance junction-case | 0.5 | $^\circ\text{C/W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-amb | 62.5 | |

Table 3. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|-----------------------------------------------------------------------------------------------------------------------|-------|------|
| I_{AR} | Avalanche current, repetitive or not repetitive (pulse width limited by T_J max) | 7 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 100\text{ V}$) | 700 | mJ |

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4. On/off state

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------|-------------------------------------------------------------------------------|------|------|---------|------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$ | 600 | | | V |
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$ | | | 5 | μA |
| | | $V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$, $T_C = 125\text{ °C}^{(1)}$ | | | 100 | μA |
| I_{GSS} | Gate-body leakage current | $V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$ | | | ± 5 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 3.25 | 4 | 4.75 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}$, $I_D = 18\text{ A}$ | | 70 | 80 | $\text{m}\Omega$ |

1. Defined by design, not subject to production test.

Table 5. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------------|-------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$ | - | 2350 | - | pF |
| C_{oss} | Output capacitance | | - | 160 | - | pF |
| C_{rss} | Reverse transfer capacitance | | - | 2 | - | pF |
| $C_{oss\text{ eq.}}^{(1)}$ | Equivalent output capacitance | $V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0\text{ V}$ | - | 416 | - | pF |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz}$ open drain | - | 1.6 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 480\text{ V}$, $I_D = 36\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior) | - | 55 | - | nC |
| Q_{gs} | Gate-source charge | | - | 12 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 31 | - | nC |

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|---------------------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 300\text{ V}$, $I_D = 18\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ | - | 23 | - | ns |
| t_r | Rise time | | - | 5.5 | - | ns |
| $t_{d(off)}$ | Turn-off delay time | (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform) | - | 57 | - | ns |
| t_f | Fall time | | - | 9 | - | ns |

Table 7. Source-drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|-------------------------------------------------------------------------------------|------|------|------|---------------|
| I_{SD} | Source-drain current | | - | | 36 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 137 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 36\text{ A}$, $V_{GS} = 0\text{ V}$ | - | | 1.6 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 36\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, | - | 115 | | ns |
| Q_{rr} | Reverse recovery charge | $V_{DD} = 60\text{ V}$ | - | 0.54 | | μC |
| I_{RRM} | Reverse recovery current | (see Figure 15. Test circuit for inductive load switching and diode recovery times) | - | 9.5 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 36\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, | - | 210 | | ns |
| Q_{rr} | Reverse recovery charge | $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ | - | 2.1 | | μC |
| I_{RRM} | Reverse recovery current | (see Figure 15. Test circuit for inductive load switching and diode recovery times) | - | 20.4 | | A |

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Table 8. Gate-source Zener diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-------------------------------|-------------------------------------------------|----------|------|------|------|
| $V_{(BR)GSO}$ | Gate-source breakdown voltage | $I_{GS} = \pm 1\text{ mA}$, $I_D = 0\text{ A}$ | ± 30 | - | - | V |

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

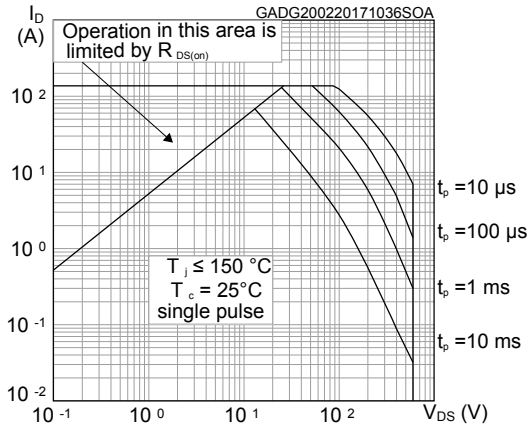


Figure 2. Thermal impedance

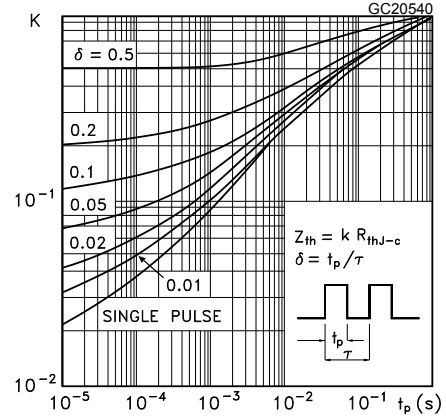


Figure 3. Output characteristics

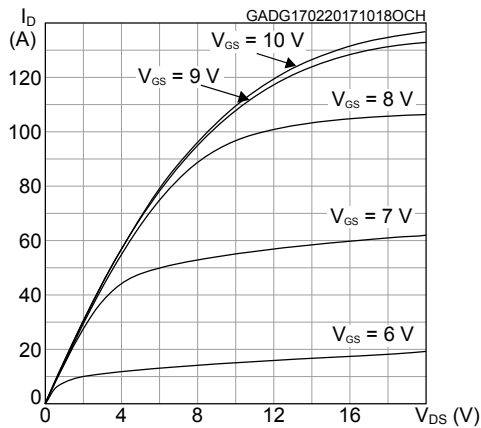


Figure 4. Transfer characteristics

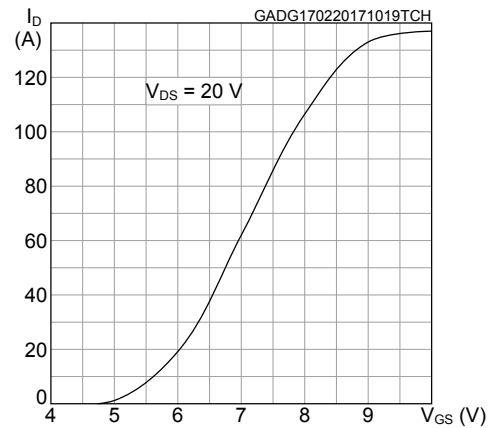


Figure 5. Gate charge vs gate-source voltage

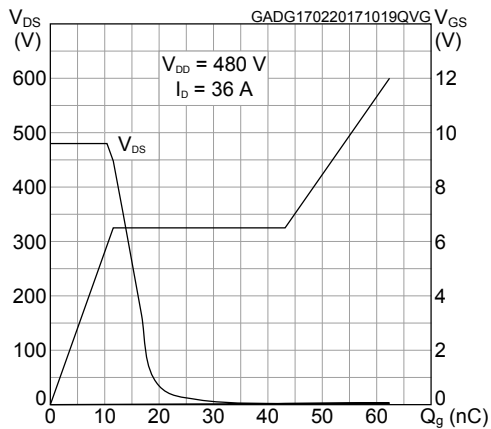


Figure 6. Static drain-source on-resistance

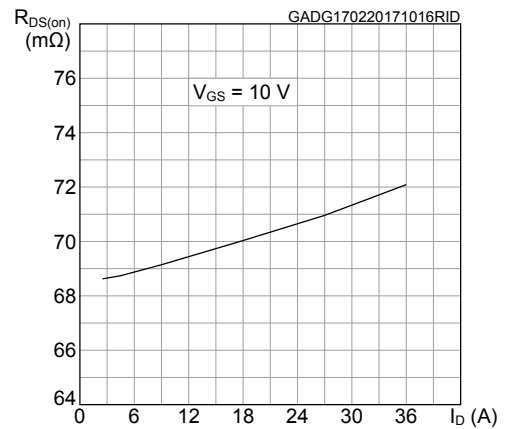


Figure 7. Capacitance variations

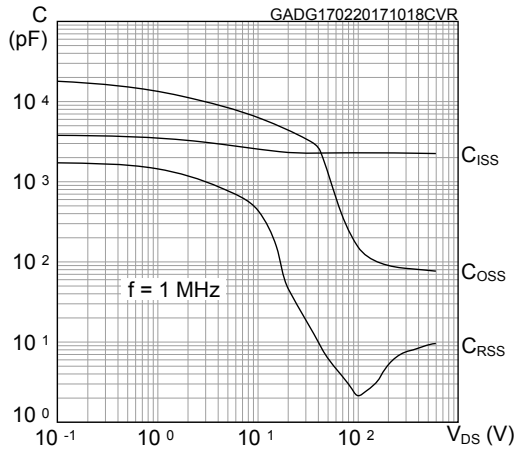


Figure 8. Normalized gate threshold voltage vs temperature

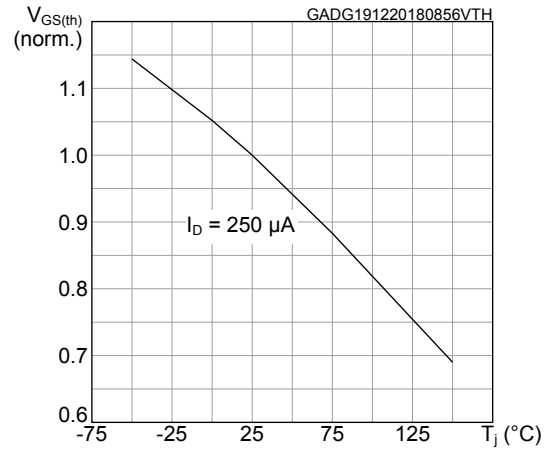


Figure 9. Normalized on-resistance vs temperature

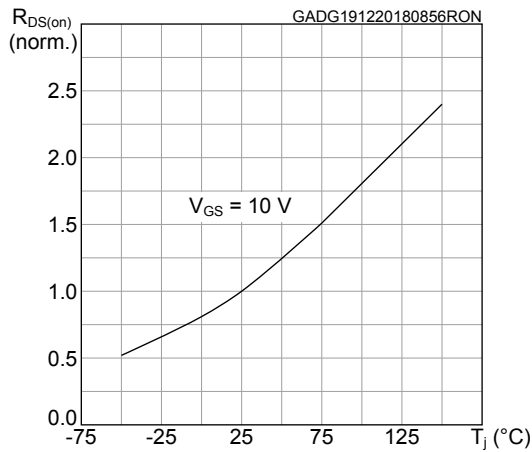


Figure 10. Normalized V_(BR)DSS vs temperature

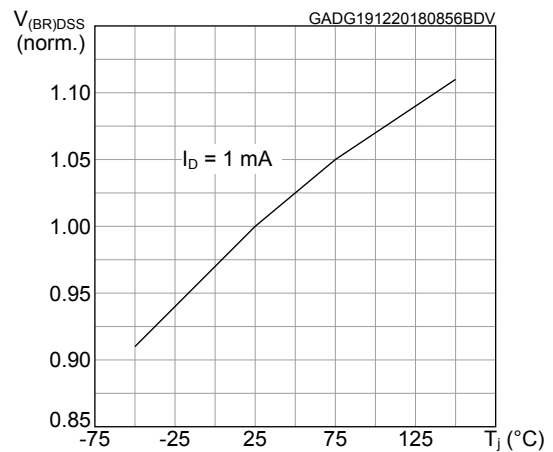


Figure 11. Source-drain diode forward characteristics

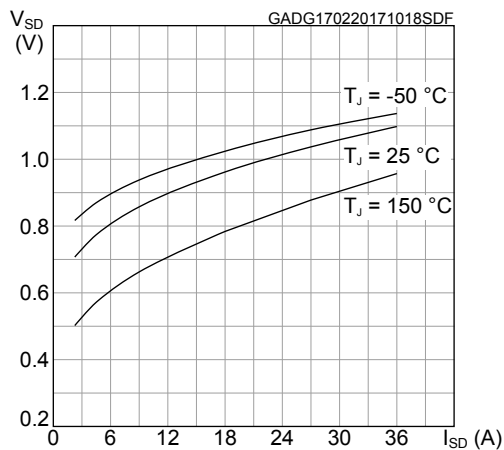
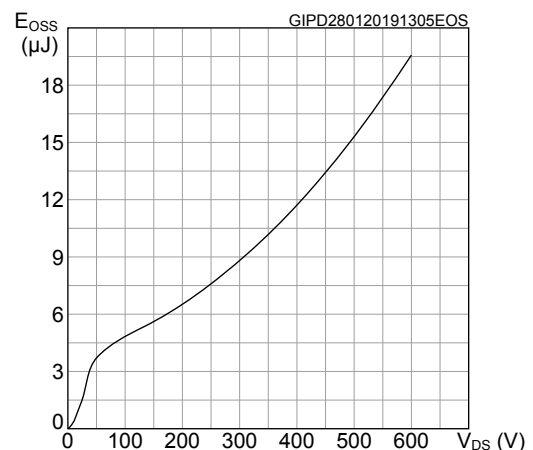
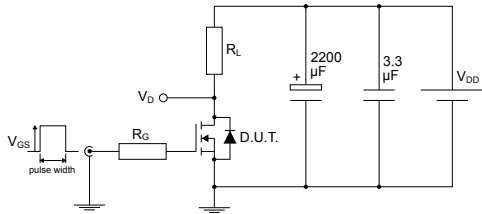


Figure 12. Output capacitance stored energy



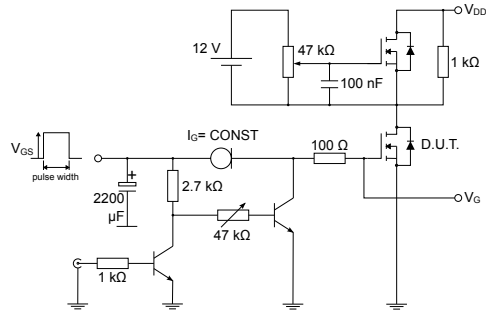
3 Test circuits

Figure 13. Test circuit for resistive load switching times



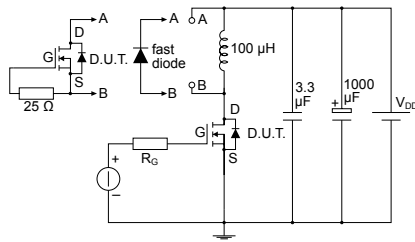
AM01468v1

Figure 14. Test circuit for gate charge behavior



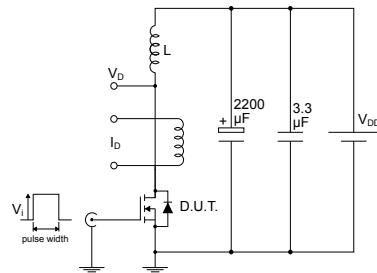
AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



AM01470v1

Figure 16. Unclamped inductive load test circuit



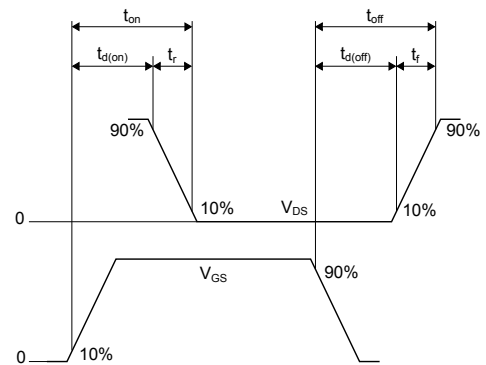
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



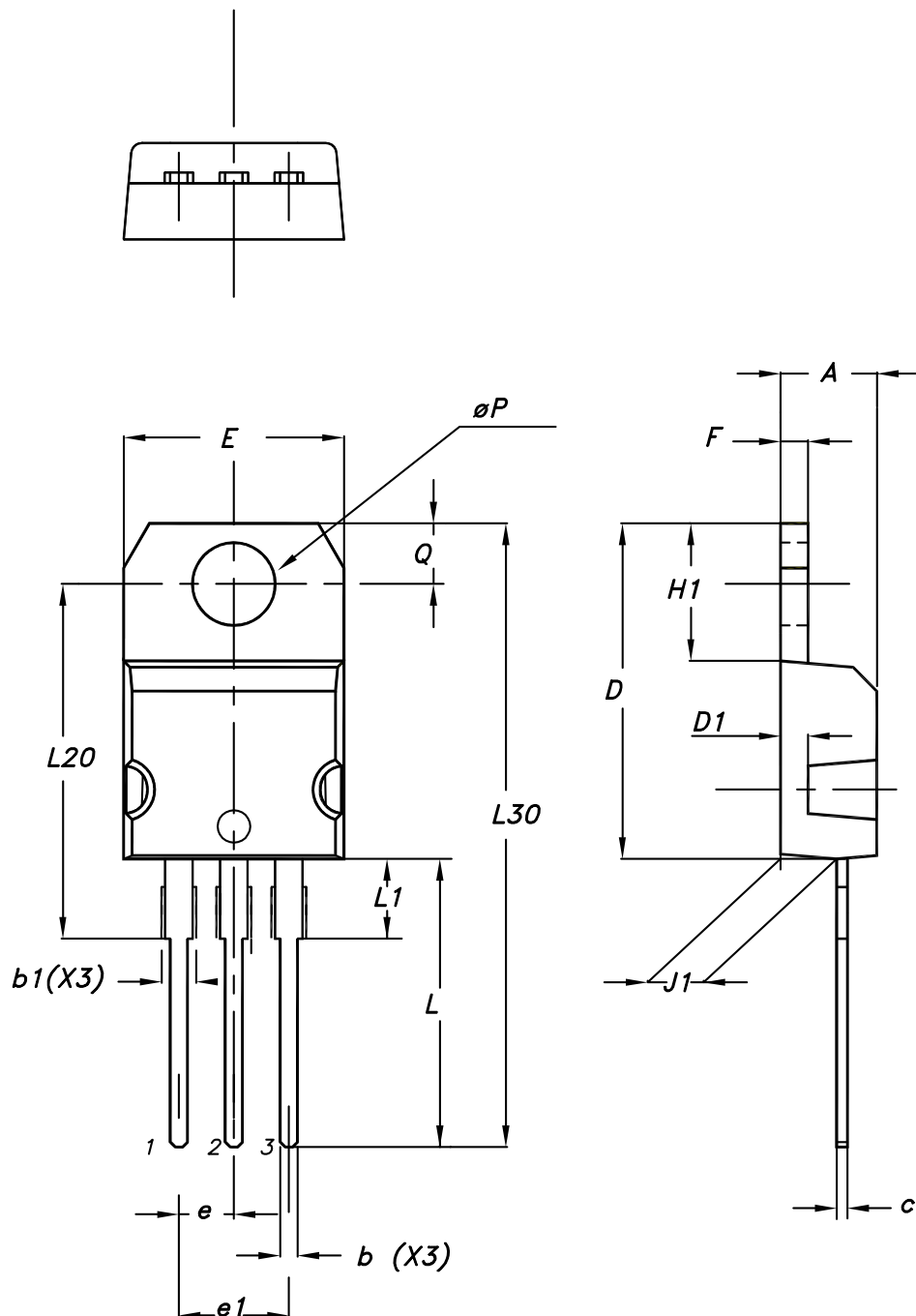
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220 type A package information

Figure 19. TO-220 type A package outline



0015988_typeA_Rev_23

Table 9. TO-220 type A package mechanical data

| Dim. | mm | | |
|---------------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| b | 0.61 | | 0.88 |
| b1 | 1.14 | | 1.55 |
| c | 0.48 | | 0.70 |
| D | 15.25 | | 15.75 |
| D1 | | 1.27 | |
| E | 10.00 | | 10.40 |
| e | 2.40 | | 2.70 |
| e1 | 4.95 | | 5.15 |
| F | 1.23 | | 1.32 |
| H1 | 6.20 | | 6.60 |
| J1 | 2.40 | | 2.72 |
| L | 13.00 | | 14.00 |
| L1 | 3.50 | | 3.93 |
| L20 | | 16.40 | |
| L30 | | 28.90 | |
| øP | 3.75 | | 3.85 |
| Q | 2.65 | | 2.95 |
| Slug flatness | | 0.03 | 0.10 |

Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|--------------------------------------------|
| 28-Feb-2019 | 1 | First release. |
| 06-Jul-2020 | 2 | Updated Table 1. Absolute maximum ratings. |

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